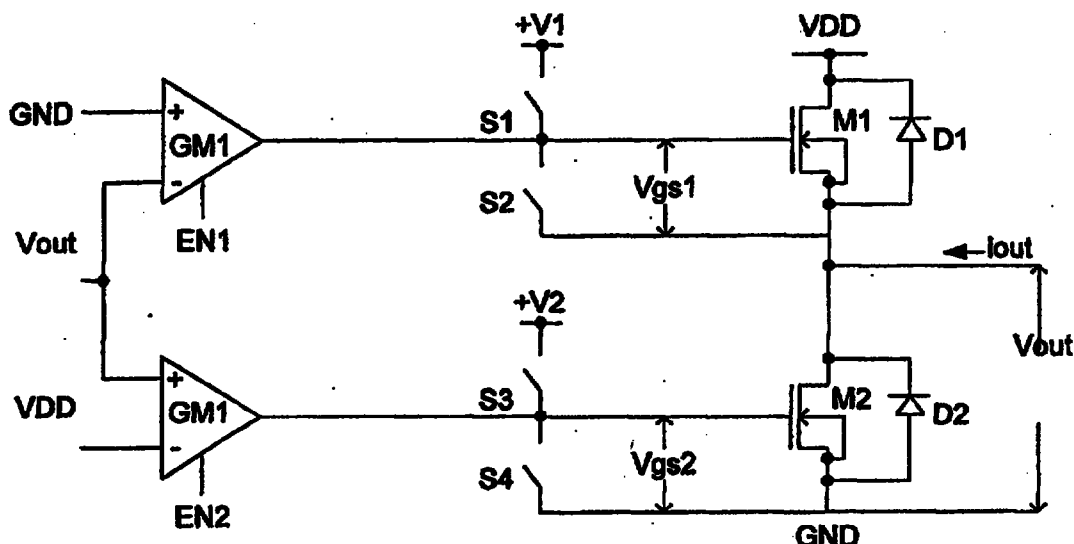




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(54) Title: METHODS AND APPARATUS FOR REDUCING MOSFET BODY DIODE CONDUCTION IN A HALF-BRIDGE CONFIGURATION

**(57) Abstract**

Methods and apparatus for operating first (M1) and second (M2) switches arranged in a half-bridge configuration are described. One of the first and second gate voltages is controlled such that the corresponding one of the first and second switches operates as a constant current source.